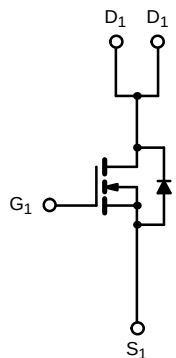
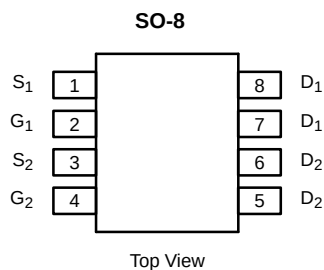


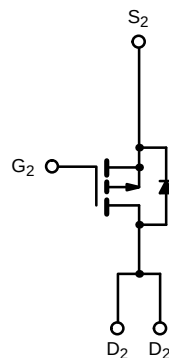


Complementary 20-V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.10 @ $V_{GS} = 10$ V	± 3.5
		0.12 @ $V_{GS} = 6$ V	± 3
		0.15 @ $V_{GS} = 4.5$ V	± 2.5
P-Channel	-20	0.10 @ $V_{GS} = -10$ V	± 3.5
		0.12 @ $V_{GS} = -6$ V	± 3
		0.19 @ $V_{GS} = -4.5$ V	± 2.5



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage			V _{DS}	20	−20	V
Gate-Source Voltage			V _{GS}	± 20	± 20	
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C		I _D	± 3.5	± 3.5	A
	T _A = 70°C			± 2.8	± 2.8	
Pulsed Drain Current			I _{DM}	± 14	± 14	
Continuous Source Current (Diode Conduction) ^a			I _S	1.7	−1.7	
Maximum Power Dissipation ^a	T _A = 25°C		P _D	2.0		W
	T _A = 70°C			1.3		
Operating Junction and Storage Temperature Range			T _J , T _{stg}	−55 to 150		°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	N- or P-Channel	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	62.5	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition		Min	Typ ^a	Max	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1.0			V
		V _{DS} = V _{GS} , I _D = −250 μA	P-Ch	−1.0			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V				±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = −16 V, V _{GS} = 0 V	P-Ch			−1	
		V _{DS} = 10 V, V _{GS} = 0 V, T _J = 70 °C	N-Ch			5	
		V _{DS} = −10 V, V _{GS} = 0 V, T _J = 70 °C	P-Ch			−5	
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	N-Ch	14			A
		V _{DS} ≤ −5 V, V _{GS} = −10 V	P-Ch	−14			
		V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	3.5			
		V _{DS} ≤ −5 V, V _{GS} = −4.5 V	P-Ch	−2.5			
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 3.5 A	N-Ch			0.10	Ω
		V _{GS} = −10 V, I _D = 3.5 A	P-Ch			0.10	
		V _{GS} = 6 V, I _D = 3 A	N-Ch			0.12	
		V _{GS} = −6 V, I _D = 3 A	P-Ch			0.12	
		V _{GS} = 4.5 V, I _D = 2 A	N-Ch			0.15	
		V _{GS} = −4.5 V, I _D = 2 A	P-Ch			0.19	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 3.5 A	N-Ch		5.6		S
		V _{DS} = −15 V, I _D = −3.5 A	P-Ch		4.0		
Diode Forward Voltage ^b	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	N-Ch		0.9	1.2	V
		I _S = −1.7 A, V _{GS} = 0 V	P-Ch		−0.9	−1.2	
Dynamic ^a							
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 10 V, I _D = 3.5 A P-Channel V _{DS} = −10 V, V _{GS} = −10 V, I _D = −3.5 A	N-Ch		9	30	nC
Gate-Source Charge	Q _{gs}		P-Ch		13	30	
			N-Ch		1.0		
Gate-Drain Charge	Q _{gd}		P-Ch		2.0		
		N-Ch		3.1			
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω P-Channel V _{DD} = −10 V, R _L = 10 Ω I _D ≅ −1 A, V _{GEN} = −10 V, R _G = 6 Ω	P-Ch		5.4		
			N-Ch		5	10	
P-Ch			21	40			
Rise Time	t _r		N-Ch		12	25	
			P-Ch		12	25	
Turn-Off Delay Time	t _{d(off)}		N-Ch		17	30	
			P-Ch		12	30	
Fall Time	t _f		N-Ch		9	20	
			P-Ch		11	20	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = 3.5 A, di/dt = 100 A/μs	N-Ch		60	100
			P-Ch		50	100	

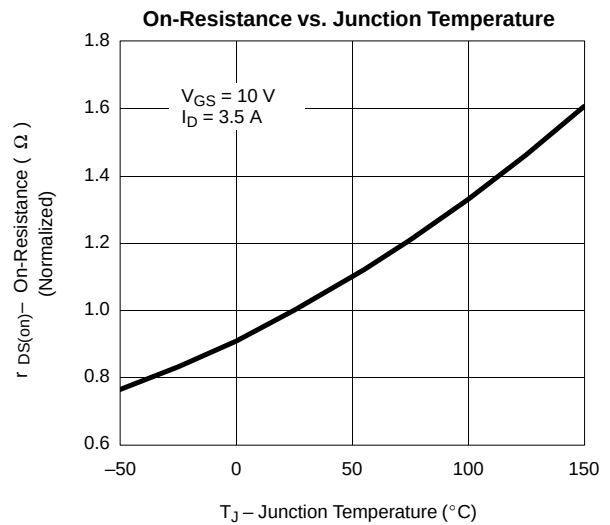
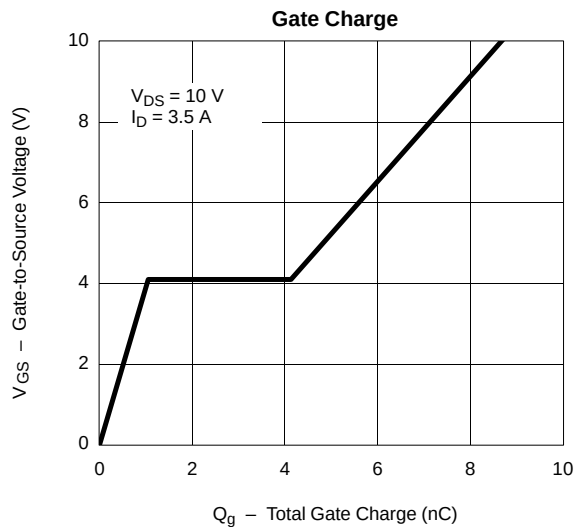
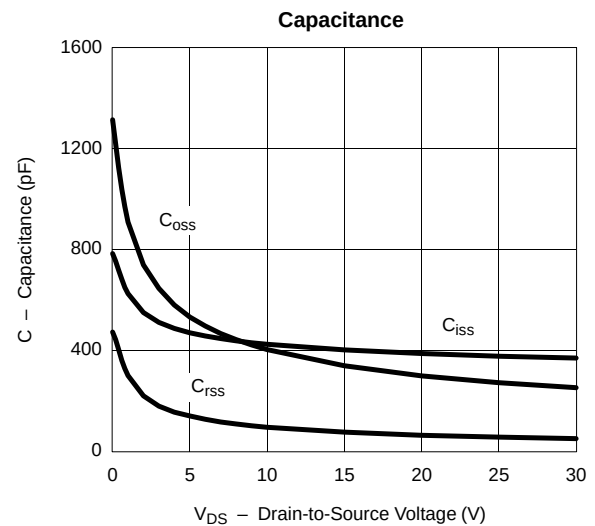
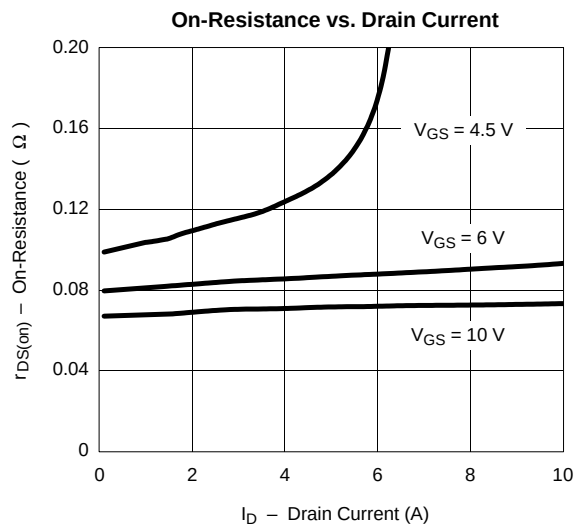
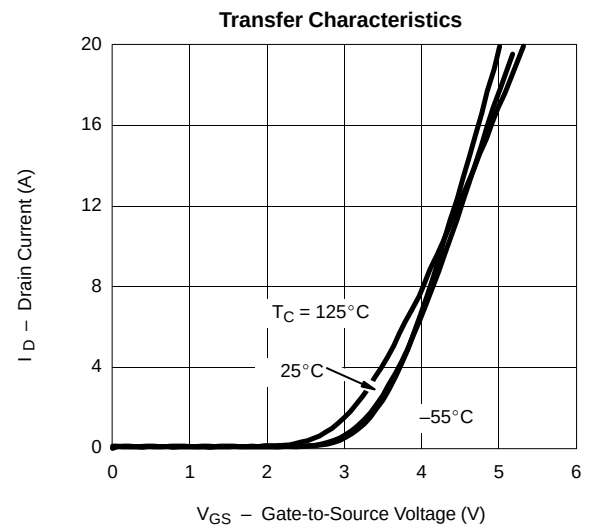
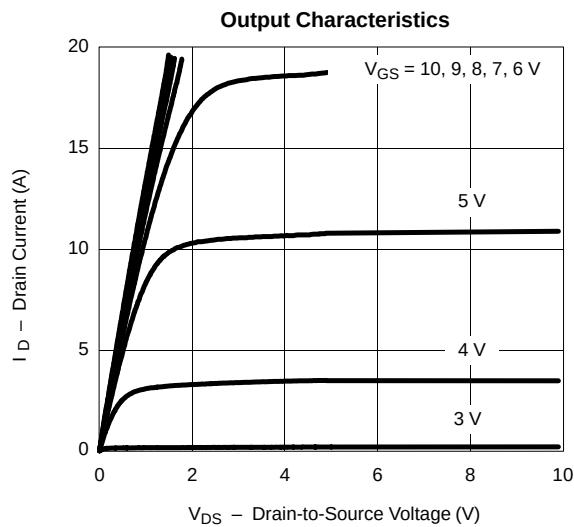
Notes

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



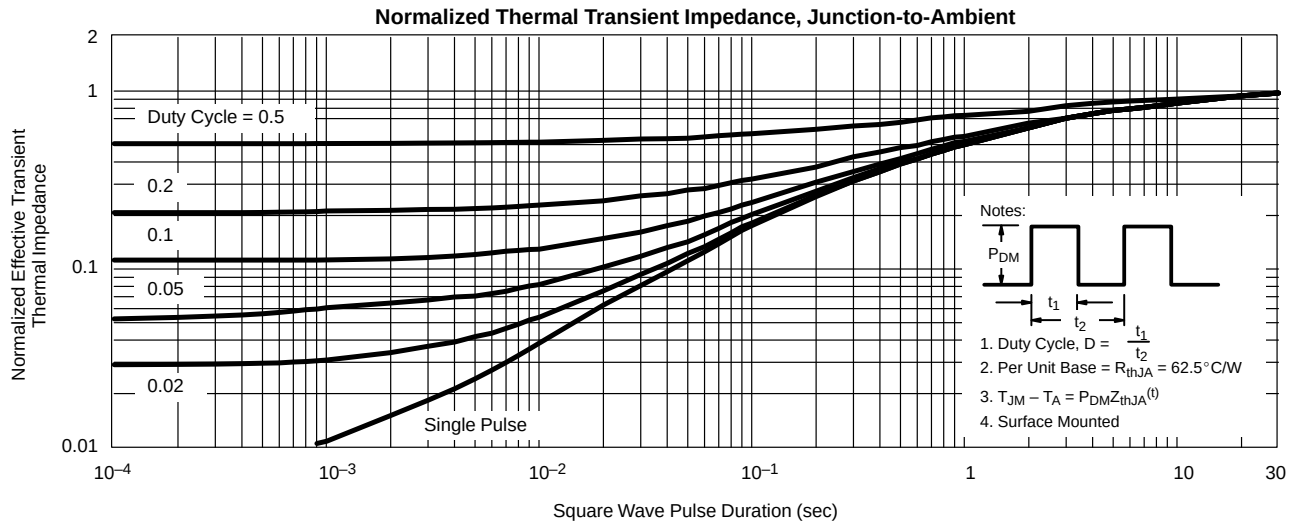
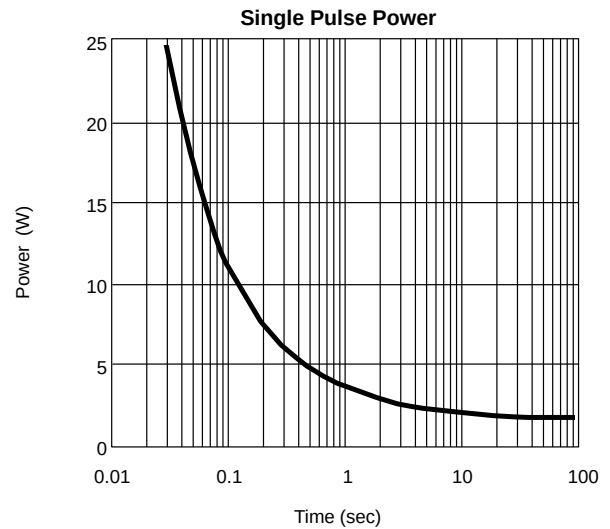
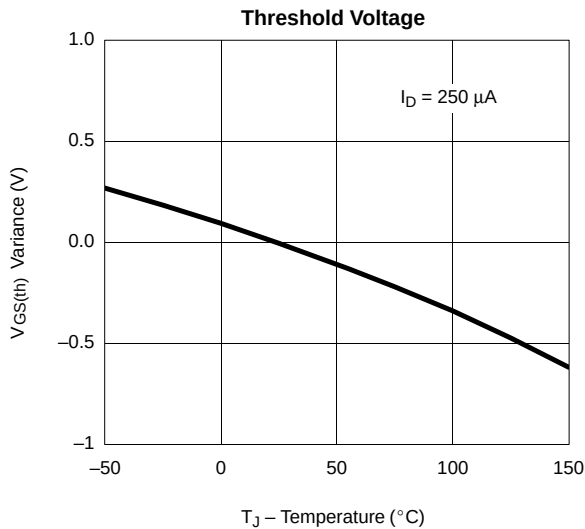
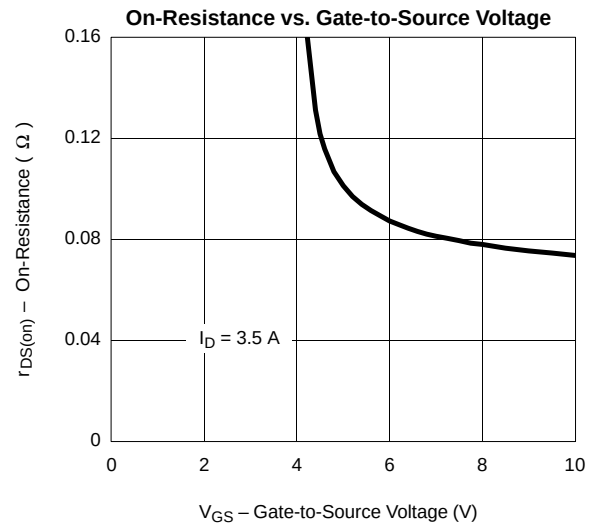
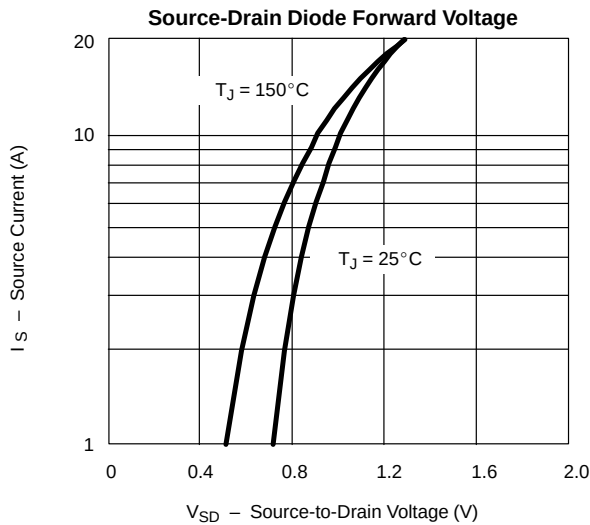
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

N-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

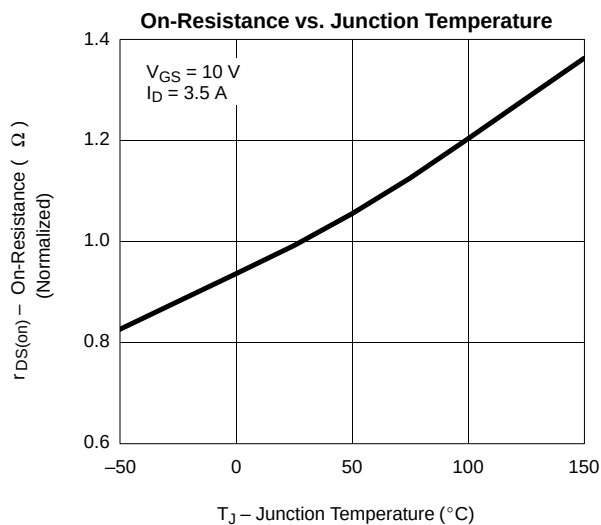
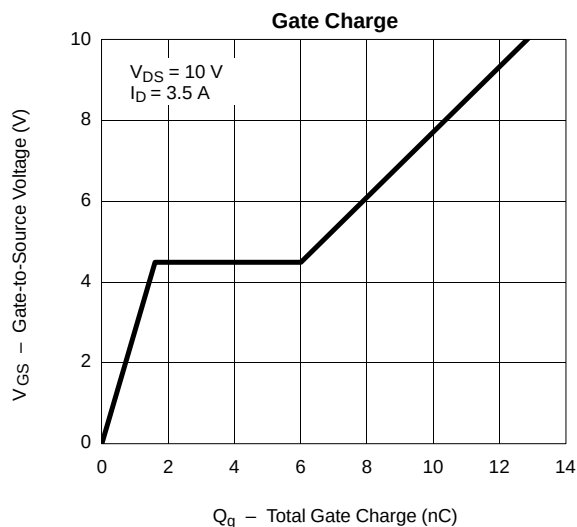
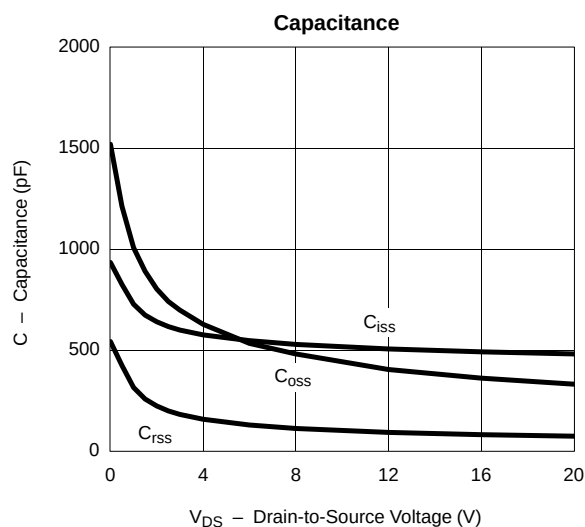
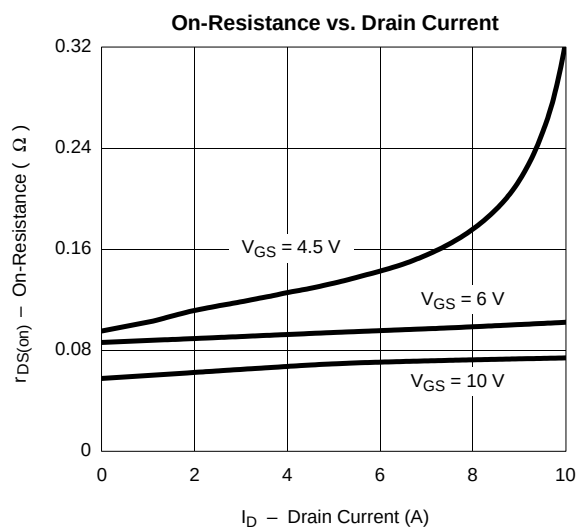
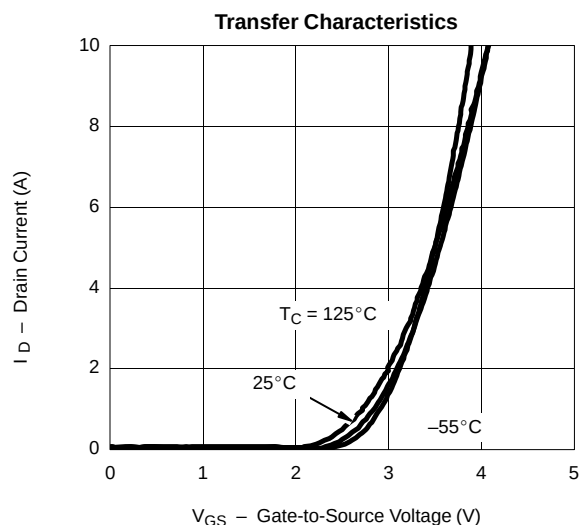
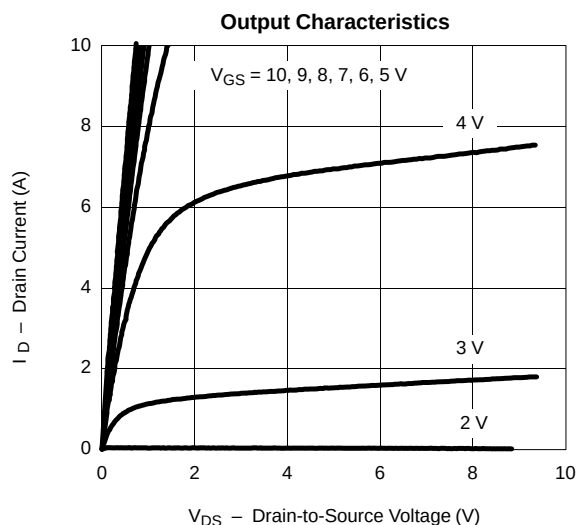
N-CHANNEL





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

P-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

P-CHANNEL

